

TYPE NUMBER	DESCRIPTION Additional information	RATINGS AND CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$, unless otherwise stated)				
		Symbol	Value	Unit	min typ max	MEASURING CONDITIONS
BP100	PHOTO-DIODE Outlines : NS216 E with colour temperature of 2400 °K	V_R V_o I_s S λ_{pk} t_r C_j A I	1 150 50 35 0,85 4 1 7 10	V mV μA nA/lx μm μs nF mm^2 μA	max min typ min typ typ typ typ max	at $E = 100 lx$ at $E = 1000 lx$ at I_s at 60% of I_s at $V_R = 0$ at $V_R = 1 V$; $E = 0$
BP101	NPN PHOTO-TRANSISTOR Outlines : 110a, with lens on top I _{ph} (at $V_{CE} = 5 V$; $E = 1000 lx$) Group I : 63 - 125 μA Group II : 100 - 200 μA Group III : 160 - 320 μA Group IV : 250 - 500 μA E with colour temperature of 2850 °K	V_{CEO} V_{EBO} I_C T_j P_{tot} I_{CEO} λ_{pk} $t_r = t_f$	32 5 25 125 200 100 0,78 10	V V mA $^{\circ}C$ mW nA μm μs	max max max max max max max max	at $V_{CE} = 30 V$; $E = 0$ at $R_L = 1 k\Omega$; $E = 1000 lx$; Open base
BP102	NPN PHOTO-TRANSISTOR Outlines : =110a, with lens on top I _{ph} (at $V_{CE} = 5 V$; $E = 1000 lx$) Group I : 160 - 320 μA Group II : 250 - 500 μA Group III : 400 - 800 μA Group IV : 630 - 1250 μA E with colour temperature of 2856 °K	V_{CEO} V_{EBO} I_C T_j P_{tot} V_{CEsat} λ_{pk} $t_r = t_f$	32 5 25 125 200 0,4 0,78 10	V V mA $^{\circ}C$ mW V μm μs	max max max max max max typ max	at $I_C = 0,5 mA$; $I_B = 25 \mu A$; $E = 0$ at $R_L = 1 k\Omega$; $I_L = 1 mA$; $V_{CE} = 25 V$
BP103	NPN PHOTO-TRANSISTOR Outlines : =110a, with lens on top I _{ph} (at $V_{CE} = 5 V$; $E = 1000 lx$) Group I : 160 - 320 μA Group II : 250 - 500 μA Group III : 400 - 800 μA Group IV : 630 - 1250 μA E with colour temperature of 2856 °K	V_{CEO} V_{EBO} I_C T_C P_j P_{tot} I_{CEO} V_{CEsat} λ_{pk} $t_r = t_f$	100 7 100 80 200 200 5 0,15 850 5	V V V $^{\circ}C$ mW mW nA V nm μs	max max max max max max max max max max	at $T = 25^{\circ}C$ at $V_{CE} = 30 V$; $E = 0$ at $I_C = 500 \mu A$; $I_B = 25 \mu A$; $E = 0$ at $R_L = 1 k\Omega$
BP104	Si-PIN PHOTO DIODE Outlines : NS365	V_R P_{tot} S λ_s I_k $t_r = t_f$ C_o I_R	15 150 35 850 5 125 55 30	V mW nA/lx nm μA ns pF nA	max max min max max max max max	at $T = 25^{\circ}C$ at $V_R = 5V$ at $E_V = 100 lx$ at $R_L = 1k\Omega$; $V_R = 0V$; $\lambda = 950nm$ at $V_R = 0V$; $f = 1MHz$; $E = 0$ at $V_R = 10V$
BPW12	PN PHOTO-VOLTAIC CELL Outlines : 110c, with plane window E with colour temperature of 2856 °K	V_R V_o I_s λ_{pk} A C_j $t_r = t_f$	10 250 7 0,75 2,8 1 3	V mV μA μm mm^2 nF μs	max min min typ typ typ typ	at $E = 1000 lx$ at $E = 1000 lx$ at $V_R = 0 V$ at $R_L = 1 k\Omega$; $I_{ph} = 100 \mu A$